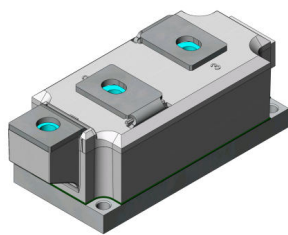


SKKT 570, SKKH 570



SEMIPACK[®] 5

Thyristor / Diode Modules

SKKT 570, SKKH 570

Target Data

Features

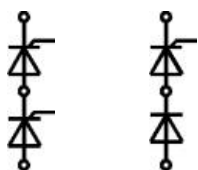
- Heat transfer through aluminium nitride ceramic insulated metal baseplate
- Hard soldered joints for high reliability
- UL recognition pending

Typical Applications

- AC motor softstarters
- Input converters for AC inverter drives
- DC motor control (e.g. for machine tools)
- Temperature control (e.g. for ovens, chemical, processes)
- Professionals light dimming (studios, theaters)

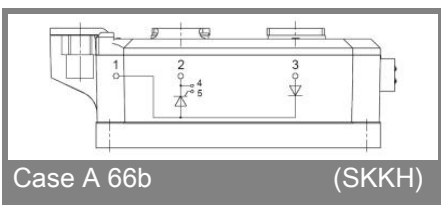
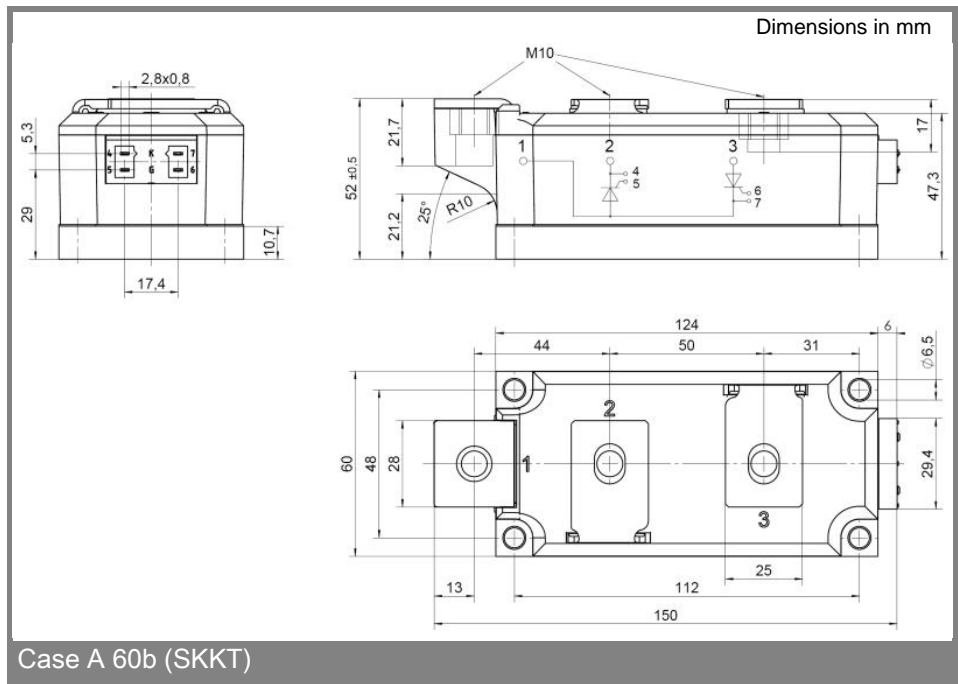
V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 1000$ A (maximum value for continuous operation) $I_{TAV} = 570$ A (sin. 180; $T_c = 85$ °C)	
1300	1200	SKKT 570/12 E	SKKH 570/12 E
1700	1600	SKKT 570/16 E	SKKH 570/16 E
1900	1800	SKKT 570/18 E	SKKH 570/18 E

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 85$ (100) °C;	570 (435)	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms $T_{vj} = 135$ °C; 10 ms	19000 15500	A
i^2t	$T_{vj} = 25$ °C; 8,3 .. 10 ms $T_{vj} = 135$ °C; 8,3 ... 10 ms	1805000 1201250	A ² s A ² s
V_T	$T_{vj} = 25$ °C; $I_T = 1700$ A	max. 1,44	V
$V_{T(TO)}$	$T_{vj} = 135$ °C	max. 0,78	V
r_T	$T_{vj} = 135$ °C	max. 0,32	mΩ
I_{DD}, I_{RD}	$T_{vj} = 135$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 200	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
t_{gr}	$V_D = 0,67 * V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 135$ °C	max. 250	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 135$ °C	max. 1000	V/μs
t_q	$T_{vj} = 135$ °C ,		μs
I_H	$T_{vj} = 25$ °C; typ. / max.	150 / 500	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	300 / 2000	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 3	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 200	mA
V_{GD}	$T_{vj} = 135$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 135$ °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,069 / 0,034	K/W
$R_{th(j-c)}$	sin. 180°; per thyristor / per module	0,072 / 0,036	K/W
$R_{th(j-c)}$	rec. 120°; per thyristor / per module	0,077 / 0,038	K/W
$R_{th(c-s)}$	per thyristor / per module	0,02 / 0,01	K/W
T_{vj}		- 40 ... + 135	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a.c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15% ¹⁾	Nm
M_t	to terminals	12 ± 15% ²⁾	Nm
a		5 * 9,81	m/s ²
m	approx.	1400	g
Case	SKKT SKKH	A 60b A 66b	



SKKT

SKKH



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